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Vishay Semiconductors

COMPLIANT

HALOGEN

## Thyristor High Voltage Surface Mount Phase Control SCR, 10 A



PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub> 6.5 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V					
$V_{TM}$	< 1.15 V					
I <sub>GT</sub>	15 mA					
$T_J$	-40 to +125 °C					
Package	D <sup>2</sup> PAK (TO-263AB)					
Circuit configuration	Single SCR					

#### **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47



#### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-10TTS08S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS								
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS								
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5						
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	A					
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5						

#### Note

• T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	6.5	۸					
I <sub>RMS</sub>		10	А					
V <sub>RRM</sub> /V <sub>DRM</sub>		800	V					
I <sub>TSM</sub>		110	A					
V <sub>T</sub>	6.5 A, T <sub>J</sub> = 25 °C	1.15	V					
dV/dt		150	V/µs					
dl/dt		100	A/µs					
T <sub>J</sub>	Range	-40 to +125	°C					

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-10TTS08S-M3	800	800	1.0					





ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST COI	VALUES	UNITS				
Maximum average on-state current	I <sub>T(AV)</sub>	T 110 °C 100° conduc	tion half ains wave	6.5				
Maximum RMS on-state current	I <sub>T(RMS)</sub>	$T_C = 112 ^{\circ}\text{C}, 180^{\circ} \text{ conduc}$	tion han sine wave	10	Α			
Maximum peak, one-cycle,		10 ms sine pulse, rated V <sub>F</sub>	RRM applied, T <sub>J</sub> = 125 °C	95	A			
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no volta	ge reapplied, T <sub>J</sub> = 125 °C	110				
Maximum 12t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>F</sub>	RRM applied, T <sub>J</sub> = 125 °C	45	A <sup>2</sup> s			
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine pulse, no volta	ge reapplied, T <sub>J</sub> = 125 °C	64	A <sup>2</sup> S			
Maximum I²√t for fusing	I²√t	t = 0.1 ms to 10 ms, no vo	640	A²√s				
Maximum on-state voltage drop	$V_{TM}$	6.5 A, T <sub>J</sub> = 25 °C	1.15	V				
On-state slope resistance	r <sub>t</sub>	T 105.00		17.3	mΩ			
Threshold voltage	V <sub>T(TO)</sub>	T <sub>J</sub> = 125 °C		0.85	V			
Maximum reverse and direct leakage current	1 /1	T <sub>J</sub> = 25 °C	\/	0.05				
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = rated V <sub>RRM</sub> /V <sub>DRM</sub>	1.0				
Typical holding current	I <sub>H</sub>	Anode supply = 6 V, resist $T_J = 25 ^{\circ}\text{C}$	30	mA				
Maximum latching current	ΙL	Anode supply = 6 V, resist	50					
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = \text{open}$			V/µs			
Maximum rate of rise of turned-on current	dl/dt			100	A/μs			

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P <sub>GM</sub>		8.0	W				
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV				
Maximum peak positive gate current	+I <sub>GM</sub>		1.5	Α				
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V				
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	20					
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	15	mA				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	10					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	1.2					
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	1	.,				
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	0.7	V				
Maximum DC gate voltage not to trigger	$V_{GD}$	T 105 °C V reted value	0.2	1				
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	0.1	mA				

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8	
Typical reverse recovery time	t <sub>rr</sub>	T 105 °C	3	μs
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	100	

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THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.5	°C/W					
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	oz.					
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	10TTS08S						

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

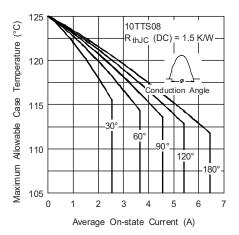


Fig. 1 - Current Rating Characteristics

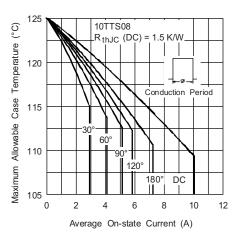


Fig. 2 - Current Rating Characteristics

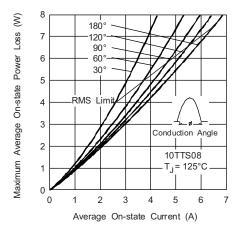


Fig. 3 - On-State Power Loss Characteristics

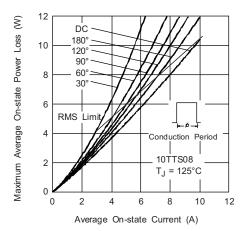


Fig. 4 - On-State Power Loss Characteristics

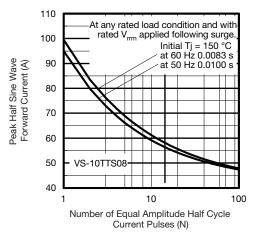


Fig. 5 - Maximum Non-Repetitive Surge Current

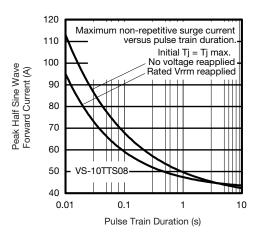


Fig. 6 - Maximum Non-Repetitive Surge Current

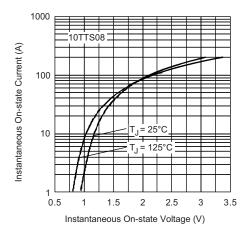


Fig. 7 - On-State Voltage Drop Characteristics

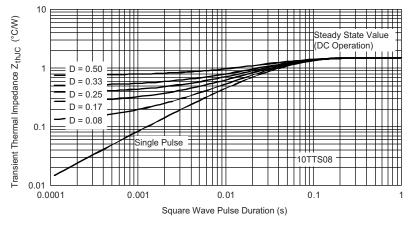
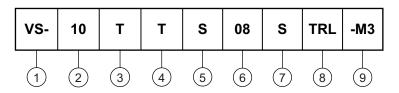


Fig. 8 - Thermal Impedance ZthJC Characteristics

### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating, RMS value

Circuit configuration:

T = single thyristor

4 - Package:

 $T = D^2PAK (TO-263AB)$ 

5 - Type of silicon:

S = converter grade

Voltage code x 100 = V<sub>RRM</sub>

7 - S = surface mountable

8 - Tape and reel option:

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

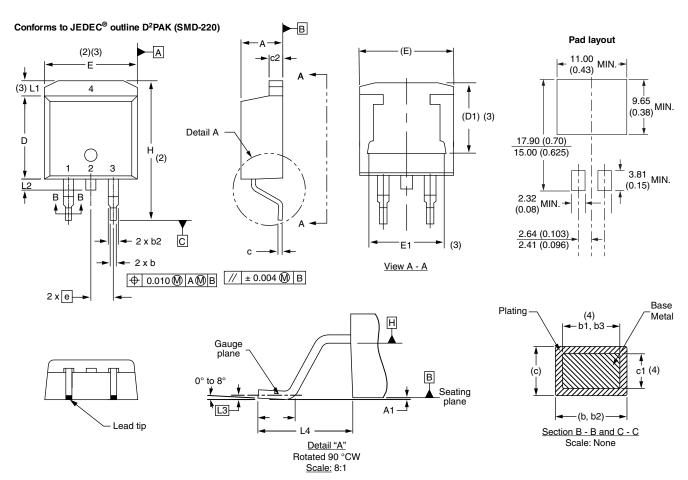
ORDERING INFORMATION (Example)								
PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION								
VS-10TTS08S-M3	50	Antistatic plastic tubes						
VS-10TTS08STRL-M3	800	13" diameter plastic tape and reel						
VS-10TTS08STRR-M3	800	13" diameter plastic tape and reel						

LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96164</u>						
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?96424					



### D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES		SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



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